TOSHIBA

MICROWAVE POWER GaAs FET TIM5359-16UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- **·BROAD BAND INTERNALLY MATCHED FET**
- ·HIGH POWER
 - P1dB= 42.5dBm at 5.3GHz to 5.9GHz
- ·HIGH GAIN
- G1dB= 10.0dB at 5.3GHz to 5.9GHz
- ·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 3.6A f = 5.3 to 5.9GHz	dBm	41.5	42.5	
Power Gain at 1dB Gain Compression Point	G1dB		dB	9.0	10.0	
Drain Current	IDS1		А		4.4	5.0
Gain Flatness	ΔG		dB			±0.6
Power Added Efficiency	ηadd		%		36	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 31.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-44	-47	
Drain Current	IDS2		А	_	4.4	5.0
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C			80

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 68 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

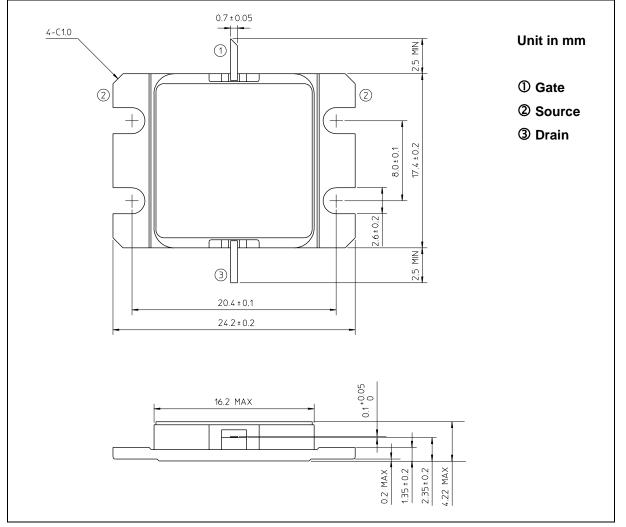
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 6.0A	S	_	3.6	
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 60mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		10.5	
Gate-Source Breakdown Voltage	VGSO	IGS= -200µA	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.5	1.8

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	14.0
Total Power Dissipation (Tc= 25°C)	PT	W	83.3
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

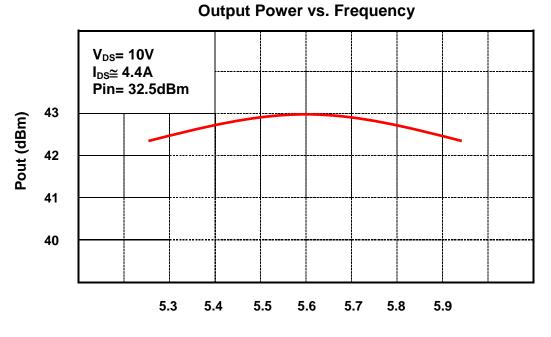
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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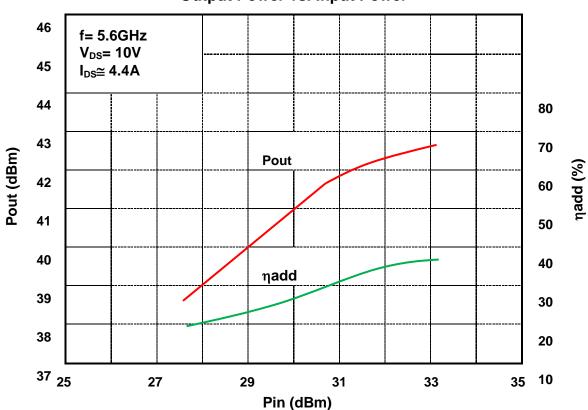
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RF PERFORMANCE



Frequency (GHz)



Output Power vs. Input Power

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

